L Number	Hits	Search Text	DB	Time stamp
_	90852		USPAT;	2004/09/28 09:45
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	27027		IBM_TDB	2004/09/28 09:45
-	37207	low near3 ((dielectric adj3 constant) or	USPAT;	2004/09/28 09:45
		k)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1583994	oxide or dioxide or sio or "sio.sub."\$2	USPAT;	2004/09/27 15:02
			US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	454908	,	USPAT;	2004/09/27 15:46
		sio or "sio.sub."\$2)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	105474		IBM_TDB	2004/00/27 15:05
-	125474	silicon adj3 carbide or sic	USPAT; US-PGPUB;	2004/09/27 15:05
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	199881	silicon adj3 nitride or "si.sub.3 n.sub.4"	USPAT;	2004/09/27 15:07
		or "si.sub.3n.sub.4" or sin	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1645043	adhe\$6	USPAT;	2004/09/28 15:18
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT; IBM TDB	
i _	294339	rf or radio adj3 frequency	USPAT;	2004/09/27 16:44
_	294339	II of facto adjointequency	US-PGPUB;	2004/03/2/ 10.44
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	294826	carbon adj2 (oxide or dioxide) or	USPAT;	2004/09/27 15:31
		"co.sub.2"	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1567600	dialactuis on inquistant on inquisting or	IBM_TDB	2004/09/28 09:43
-	1557693	dielectric or insulator or insulating or insulation	USPAT; US-PGPUB;	2004/09/20 09:43
		Insulacion	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	83646	adhe\$6 with (dielectric or insulator or	USPĀT;	2004/09/27 15:49
		insulating or insulation)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		, , , , , , , , , , , , , , , , , , , ,	IBM_TDB	0004/00/07 25 :5
-	6696		USPAT;	2004/09/27 15:47
		dioxide or sio or "sio.sub."\$2)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	11926	((c or carbon) with dop\$4 with (oxide or	USPAT;	2004/09/27 15:48
	11,23	dioxide or sio or "sio.sub."\$2)) or sioc	US-PGPUB;	
		or cdo	EPO; JPO;	
	Ì		DERWENT;	
			IBM_TDB	
-	636		USPAT;	2004/09/27 15:51
		insulating or insulation)) and (((c or	US-PGPUB;	
		carbon) with dop\$4 with (oxide or dioxide	EPO; JPO;	
İ		or sio or "sio.sub."\$2)) or sioc or cdo)	DERWENT;	
			IBM TDB	<u> </u>

				•
-	207	((adhe\$6 with (dielectric or insulator or	USPAT;	2004/09/27 15:50
	ŀ	insulating or insulation)) and (((c or	US-PGPUB;	
		carbon) with dop\$4 with (oxide or dioxide	EPO; JPO;	
		or sio or "sio.sub."\$2)) or sioc or cdo))	DERWENT;	
1_	23	and (rf or radio adj3 frequency) adhe\$6 with (((c or carbon) with dop\$4	IBM_TDB USPAT;	2004/09/27 16:04
-	23	with (oxide or dioxide or sio or	US-PGPUB;	2004/09/27 10:04
		"sio.sub."\$2)) or sioc or cdo) with	EPO; JPO;	
		((silicon adj3 carbide or sic) or (silicon	DERWENT;	
		adj3 nitride or "si.sub.3 n.sub.4" or	IBM TDB	
		"si.sub.3n.sub.4" or sin))		
-	4446	(USPAT;	2004/09/27 16:05
		insulating or insulation)) and (low near3	US-PGPUB;	
		((dielectric adj3 constant) or k))	EPO; JPO;	
			DERWENT; IBM TDB	
_	981	((adhe\$6 with (dielectric or insulator or	USPAT;	2004/09/27 16:06
		insulating or insulation)) and (low near3	US-PGPUB;	
		((dielectric adj3 constant) or k))) and	EPO; JPO;	
		(rf or radio adj3 frequency)	DERWENT;	
			IBM_TDB	
-	156	1 ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPAT;	2004/09/27 16:09
		insulating or insulation)) and (low near3 ((dielectric adj3 constant) or k))) and	US-PGPUB; EPO; JPO;	
		(rf or radio adj3 frequency)) and (((c or	DERWENT;	
		carbon) with dop\$4 with (oxide or dioxide	IBM TDB	
		or sio or "sio.sub."\$2)) or sioc or cdo)		
-	72	1 ((()))	USPAT;	2004/09/27 16:45
		insulating or insulation)) and (low near3	US-PGPUB;	
		((dielectric adj3 constant) or k))) and	EPO; JPO;	
		(rf or radio adj3 frequency)) and (((c or carbon) with dop\$4 with (oxide or dioxide	DERWENT;	
		or sio or "sio.sub."\$2)) or sioc or cdo)	IBM_TDB	
		and (carbon adj2 (oxide or dioxide) or		
		"co.sub.2")		
-	37207	low near3 ((dielectric adj3 constant) or	USPAT;	2004/09/27 17:14
		k)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
l _	1481	438/778.ccls. or 438/788.ccls.	USPĀT;	2004/09/27 17:16
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
	1726	/430/770 colo om 430/700 colo \ om	IBM_TDB	2004/00/27 17.17
-	1736	(438/778.ccls. or 438/788.ccls.) or 438/790.ccls.	USPAT; US-PGPUB;	2004/09/27 17:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	535	(low near3 ((dielectric adj3 constant) or	USPAT;	2004/09/27 17:17
		k)) and ((438/778.ccls. or 438/788.ccls.) or 438/790.ccls.)	US-PGPUB;	
1		OI 430//90.CCIS.)	EPO; JPO; DERWENT;	
			IBM TDB	
-	1645043	adhe\$6	USPAT;	2004/09/27 17:17
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	244	((low near3 ((dielectric adj3 constant) or	IBM_TDB USPAT;	2004/09/27 17:58
	244	k)) and ((438/778.ccls. or 438/788.ccls.)	US-PGPUB;	2003/03/21 11.30
		or 438/790.ccls.)) and adhe\$6	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1257339	(upper or top or first or second) near3	USPAT;	2004/09/27 18:00
		portion	US-PGPUB; EPO; JPO;	
			DERWENT;	
1			IBM TDB	
	 			

				· · · · · · · · · · · · · · · · · · ·
-	1226898	(lower or bottom or first or second) near3	USPAT;	2004/09/27 18:01
		portion	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	937920	((upper or top or first or second) near3	USPAT;	2004/09/27 18:02
		portion) same ((lower or bottom or first	US-PGPUB;	
		or second) near3 portion)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	308	((upper or top or first or second) near3	USPAT;	2004/09/27 18:02
		portion) with (low near3 ((dielectric adj3	US-PGPUB;	
		constant) or k))	EPO; JPO; DERWENT;	
			IBM TDB	
_	287	((lower or bottom or first or second)	USPAT;	2004/09/27 18:02
		near3 portion) with (low near3	US-PGPUB;	
		((dielectric adj3 constant) or k))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	239		USPAT;	2004/09/27 18:02
		portion) with (low near3 ((dielectric adj3	US-PGPUB;	
		constant) or k))) same (((lower or bottom	EPO; JPO;	
		or first or second) near3 portion) with (low near3 ((dielectric adj3 constant) or	DERWENT; IBM TDB	
		(low hears ((drefectife adjs constant) of k)))	1514-106	
-	90	1 ' ' '	USPAT;	2004/09/27 18:02
		portion) with (low near3 ((dielectric adj3	US-PGPUB;	2001, 03, 27 20102
		constant) or k))) same (((lower or bottom	EPO; JPO;	
		or first or second) near3 portion) with	DERWENT;	
		(low near3 ((dielectric adj3 constant) or	IBM_TDB	
	40	k)))) and adhe\$6		0004/00/55 55 55
-	101429		USPAT;	2004/09/28 11:02
		adj3 layer	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1555600	di\$1electric or insulator or insulating or	USPAT;	2004/09/28 09:44
		insulation	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	8166	,,,,,	USPAT;	2004/09/28 09:44
		adj3 layer) with (di\$lelectric or insulator or insulating or insulation)	US-PGPUB; EPO; JPO;	
		insurator of insurating of insuration)	DERWENT;	
			IBM TDB	
-	1999872	(dielectric adj3 constant) or k	USPAT;	2004/09/28 09:45
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/00 55 55
-	37257	low near3 ((dielectric adj3 constant) or	USPAT;	2004/09/28 09:46
		(k)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	12369	grad\$4 near5 (di\$1electric or k or	USPAT;	2004/09/28 09:47
		constant)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	00400	(0.101)	IBM_TDB	0004/00/00 00 10
_	20428	((bi\$1layer or dual\$1layer or composit\$3	USPAT;	2004/09/28 09:48
		adj3 layer) with (di\$lelectric or insulator or insulating or insulation))	US-PGPUB;	
		or (grad\$4 near5 (di\$lelectric or k or	EPO; JPO; DERWENT;	
		constant))	IBM TDB	
L	L	1 30		<u> </u>

_	1404	(((bi\$1layer or dual\$1layer or composit\$3 adj3 layer) with (di\$1electric or	USPAT; US-PGPUB;	2004/09/28 09:48
		insulator or insulating or insulation)) or (grad\$4 near5 (di\$1electric or k or	EPO; JPO; DERWENT;	
		constant))) and (low near3 ((dielectric adj3 constant) or k))	IBM_TDB	
-	1170204	damascence or cu or copper	USPAT; US-PGPUB;	2004/09/28 09:49
			EPO; JPO; DERWENT;	
	18215	(inter\$llayer near4 di\$lelectric) or ild	IBM_TDB USPAT;	2004/09/28 09:51
	10213	or idl	US-PGPUB;	2004/03/28 03.31
			EPO; JPO; DERWENT;	
-	202	((((bi\$llayer or dual\$llayer or composit\$3	IBM_TDB USPAT;	2004/09/28 09:51
		adj3 layer) with (di\$lelectric or insulator or insulating or insulation))	US-PGPUB; EPO; JPO;	
		or (grad\$4 near5 (di\$1electric or k or constant))) and (low near3 ((dielectric	DERWENT; IBM_TDB	
		adj3 constant) or k))) and ((inter\$1layer near4 di\$1electric) or ild or idl)		
-	159	<pre>(((((bi\$1layer or dual\$1layer or composit\$3 adj3 layer) with (di\$1electric</pre>	USPAT; US-PGPUB;	2004/09/28 09:51
		or insulator or insulating or insulation)) or (grad\$4 near5 (di\$1electric or k or	EPO; JPO; DERWENT;	
		<pre>constant))) and (low near3 ((dielectric adj3 constant) or k))) and ((inter\$1layer</pre>	IBM_TDB	
		near4 di\$1electric) or ild or idl)) and (damascence or cu or copper)		
-	327690	((dielectric adj3 constant) or k) adj5 (1\$2 or 2\$2 or 3\$2 or 4\$2)	USPAT; US-PGPUB;	2004/09/28 10:27
			EPO; JPO; DERWENT;	
_	868	((((bi\$llayer or dual\$llayer or composit\$3	IBM_TDB USPAT;	2004/09/28 10:12
		adj3 layer) with (di\$lelectric or insulator or insulating or insulation))	US-PGPUB; EPO; JPO;	
		or (grad\$4 near5 (di\$1electric or k or constant))) and (low near3 ((dielectric	DERWENT; IBM TDB	
		adj3 constant) or k))) and ((damascence or cu or copper) or ((inter\$llayer near4		
_	381929	di\$1electric) or ild or idl))	USPAT;	2004/09/28 10:13
	301313	2411401	US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
-	5715	((inter\$1layer near4 di\$1electric) or ild or idl) and barrier	USPAT; US-PGPUB;	2004/09/28 10:14
			EPO; JPO; DERWENT;	
_	64414	(damascence or cu or copper) and barrier	IBM_TDB USPAT;	2004/09/28 10:14
	61114	(damassense of the of copper) and buffler	US-PGPUB; EPO; JPO;	2001, 05, 20 10.11
			DERWENT; IBM TDB	
-	454	((((bi\$1layer or dual\$1layer or composit\$3 adj3 layer) with (di\$1electric or	USPAT; US-PGPUB;	2004/09/28 10:15
		insulator or insulating or insulation)) or (grad\$4 near5 (di\$1electric or k or	EPO; JPO; DERWENT;	
		constant))) and (low near3 ((dielectric adj3 constant) or k))) and	IBM_TDB	
		((((inter\$llayer near4 di\$lelectric) or ild or idl) and barrier) or ((damascence		
		or cu or copper) and barrier))		

-	611	((((((bi\$layer or dual\$layer or composit\$3 adj3 layer) with (di\$lelectric or insulator or insulating or insulation)) or (grad\$4 near5 (di\$lelectric or k or constant))) and (low near3 ((dielectric adj3 constant) or k))) and ((inter\$llayer near4 di\$lelectric) or ild or idl)) and (damascence or cu or copper)) or (((((bi\$llayer or dual\$llayer or composit\$3 adj3 layer) with (di\$lelectric or insulator or insulating or insulation)) or (grad\$4 near5 (di\$lelectric or k or constant))) and (low near3 ((dielectric adj3 constant) or k))) and ((damascence or cu or copper) or ((inter\$llayer near4 di\$lelectric) or ild or idl))) or (((((bi\$llayer or dual\$llayer or composit\$3 adj3 layer) with (di\$lelectric or insulator or insulating or insulation))) or (grad\$4 near5 (di\$lelectric or k or constant))) and (low near3 ((dielectric or insulator or insulating or insulation))) or (grad\$4 near5 (di\$lelectric or k or constant))) and (low near3 ((dielectric adj3 constant) or k))) and (((((((((((((((((((((((((((((((((((USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/28 10:15
_	311368	(1\$2 or 2\$2 or 3\$2 or 4\$2)) bi\$1layer or dual\$1layer or multi\$1layer or composit\$3 adj3 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/28 11:04
-	44430	(bi\$1layer or dual\$1layer or multi\$1layer or composit\$3 adj3 layer) with (di\$1electric or insulator or insulating or insulation)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/28 11:06
_	56502	((bi\$1layer or dual\$1layer or multi\$1layer or composit\$3 adj3 layer) with (di\$1electric or insulator or insulating or insulation)) or (grad\$4 near5 (di\$1electric or k or constant))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/28 11:06

_	4028	(((bi\$1layer or dual\$1layer or	USPAT;	2004/09/28 11:08
	1020	multi\$1layer or composit\$3 adj3 layer)	US-PGPUB;	2000,00,00
		with (di\$1electric or insulator or	EPO; JPO;	
		insulating or insulation)) or (grad\$4	DERWENT;	
		near5 (di\$lelectric or k or constant)))	IBM TDB	
		and (low near3 ((dielectric adj3 constant)	1511-155	
		or k)		
_	2552		USPAT;	2004/09/28 11:11
_	2332	multi\$11ayer or composit\$3 adj3 layer)	US-PGPUB;	2004/03/28 11:11
		with (di\$lelectric or insulator or	EPO; JPO;	
		insulating or insulation)) or (grad\$4	DERWENT;	
		near5 (di\$1electric or k or constant)))	IBM TDB	
			I TOM TIND	
		and (low near3 ((dielectric adj3 constant)		
	ļ	or k))) and ((damascence or cu or copper)		
	i	or ((inter\$1layer near4 di\$1electric) or	1	İ
	1	ild or idl))	, , ann , m	2004/00/00 11 10
-	1021	(((((bi\$1layer or dual\$1layer or	USPAT;	2004/09/28 11:12
		multi\$1layer or composit\$3 adj3 layer)	US-PGPUB;	
		with (di\$lelectric or insulator or	EPO; JPO;	
		insulating or insulation)) or (grad\$4	DERWENT;	
		<pre>near5 (di\$1electric or k or constant)))</pre>	IBM_TDB	
		and (low near3 ((dielectric adj3 constant)		
		or k))) and ((damascence or cu or copper)		
	1	or ((inter\$1layer near4 di\$1electric) or		
		ild or idl))) and ((((inter\$1layer near4		
		di\$1electric) or ild or idl) and barrier)		
		or ((damascence or cu or copper) and		
		barrier))		
-	700	(((((bi\$1layer or dual\$1layer or	USPAT;	2004/09/28 12:23
	į	multi\$1layer or composit\$3 adj3 layer)	US-PGPUB;	
	Í	with (di\$lelectric or insulator or	EPO; JPO;	
		insulating or insulation)) or (grad\$4	DERWENT;	
		near5 (di\$1electric or k or constant)))	IBM TDB	[
		and (low near3 ((dielectric adj3 constant)	_	İ
		or k))) and ((damascence or cu or copper)		
	}	or ((inter\$1layer near4 di\$1electric) or		
		ild or idl))) and ((((inter\$1layer near4		
		di\$1electric) or ild or idl) and barrier)		
		or ((damascence or cu or copper) and		
		barrier))) and (((dielectric adj3		
		constant) or k) adj5 (1\$2 or 2\$2 or 3\$2 or		
		4\$2))		
_	68907	pe\$1cvd or plasma adj6 (cvd or deposit\$4)	USPAT;	2004/09/28 12:24
		principal and the monopological	US-PGPUB;	}
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
	1			1

	032	1/////////	TIODAM.	1 2004 /00 /20 12:25
-	976	((((((((bi\$llayer or dual\$llayer or	USPAT;	2004/09/28 12:25
		composit\$3 adj3 layer) with (di\$1electric	US-PGPUB;	
		or insulator or insulating or insulation	EPO; JPO;	
)) or (grad\$4 near5 (di\$1electric or k or	DERWENT;	
		constant))) and (low near3 ((dielectric	IBM_TDB	
		adj3 constant) or k))) and ((inter\$1layer		
		near4 di\$1electric) or ild or idl)) and		
		(damascence or cu or copper)) or		
		((((bi\$llayer or dual\$llayer or		
		composit\$3 adj3 layer) with (di\$1electric		
		or insulator or insulating or insulation		
)) or (grad\$4 near5 (di\$1electric or k or		
		constant))) and (low near3 ((dielectric		
		adj3 constant) or k))) and ((damascence		
		or cu or copper) or ((inter\$1layer near4		
		di\$lelectric) or ild or idl))) or		
		(((((bi\$1layer or dual\$1layer or		
		composit\$3 adj3 layer) with (di\$1electric		
		or insulator or insulating or insulation		
)) or (grad\$4 near5 (di\$1electric or k or		
		1		
		constant))) and (low near3 ((dielectric		
		adj3 constant) or k))) and		
		((((inter\$1layer near4 di\$1electric) or		
		ild or idl) and barrier) or ((damascence		
		or cu or copper) and barrier)))) and		
		(((dielectric adj3 constant) or k) adj5		
		(1\$2 or 2\$2 or 3\$2 or 4\$2))) or	Į	
		((((((bi\$llayer or dual\$llayer or		
		multi\$1layer or composit\$3 adj3 layer)		
		with (di\$lelectric or insulator or		
		insulating or insulation)) or (grad\$4		
		<pre>near5 (di\$1electric or k or constant)))</pre>		
		and (low near3 ((dielectric adj3 constant)		
		or k))) and ((damascence or cu or copper)		
		or ((inter\$1layer near4 di\$1electric) or		
		ild or idl))) and (((inter\$1layer near4		
	1	di\$lelectric) or ild or idl) and barrier)		
		or ((damascence or cu or copper) and		
		barrier))) and (((dielectric adj3		
		constant) or k) adj5 (1\$2 or 2\$2 or 3\$2 or		

_	477	(((((((bi\$1layer or dual\$1layer or	USPAT;	2004/09/28 12:25
		composit\$3 adj3 layer) with (di\$1electric	US-PGPUB;	
		or insulator or insulating or insulation	EPO; JPO;	
Ì)) or (grad\$4 near5 (di\$1electric or k or	DERWENT;	
		constant))) and (low near3 ((dielectric	IBM TDB	
		adj3 constant) or k))) and ((inter\$1layer	150-100	
	İ	near4 di\$1electric) or ild or idl)) and		
		(damascence or cu or copper)) or		
		((((bi\$1layer or dual\$1layer or		
		composit\$3 adj3 layer) with (di\$1electric		
		or insulator or insulating or insulation		
)) or (grad\$4 near5 (di\$1electric or k or		
1		constant))) and (low near3 ((dielectric		
		adj3 constant) or k))) and ((damascence		1
		or cu or copper) or ((inter\$1layer near4		
		di\$lelectric) or ild or idl))) or		
		(((((bi\$1layer or dual\$1layer or		
		composit\$3 adj3 layer) with (di\$1electric		
		or insulator or insulating or insulation		
-	1)) or (grad\$4 near5 (di\$1electric or k or		
1		constant))) and (low near3 ((dielectric		
1		adj3 constant) or k))) and		
		((((inter\$1layer near4 di\$1electric) or		
		ild or idl) and barrier) or ((damascence		1
		or cu or copper) and barrier)))) and		
		(((dielectric adj3 constant) or k) adj5		
		(1\$2 or 2\$2 or 3\$2 or 4\$2))) or		
	ļ	((((((bi\$1layer or dual\$1layer or		
		multi\$11ayer or composit\$3 adj3 layer)		
		with (di\$lelectric or insulator or		
		insulating or insulation)) or (grad\$4		
		near5 (di\$1electric or k or constant)))		
		and (low near3 ((dielectric adj3 constant)		
		or k))) and ((damascence or cu or copper)		
		or ((inter\$1layer near4 di\$1electric) or		
	ŀ	<pre>ild or idl))) and ((((inter\$1layer near4</pre>		
		di\$lelectric) or ild or idl) and barrier)		
		or ((damascence or cu or copper) and		
		barrier))) and (((dielectric adj3		
	ļ	constant) or k) adj5 (1\$2 or 2\$2 or 3\$2 or		
		4\$2)))) and (pe\$1cvd or plasma adj6 (cvd		
1	1645012	or deposit\$4))	HCDAT.	2004/09/28 15:18
1 -	1645813	adhe\$6	USPAT;	2004/05/20 15:18
		· ·	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	28718	adhe\$6 with barrier	USPAT;	2004/09/28 15:19
1			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1			IBM TDB	
-	1687	(adhe\$6 with barrier) and (low near3	USPAT;	2004/09/28 15:20
1		((dielectric adj3 constant) or k))	US-PGPUB;	
		, , , ==== 0 + = = + = = = = = = = = = = = =	EPO; JPO;	
1			DERWENT;	
			IBM TDB	
	1400	(/adhate with hammian) and (law mann)	. —	2004/09/28 15:20
-	1480	((adhe\$6 with barrier) and (low near3	USPAT;	2004/03/20 13:20
		((dielectric adj3 constant) or k))) and	US-PGPUB;	
I		(damascence or cu or copper)	EPO; JPO;	
			DERWENT;	1
			IBM_TDB	
-	797	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2004/09/28 15:20
		((dielectric adj3 constant) or k))) and	US-PGPUB;	
		(damascence or cu or copper)) and (pe\$1cvd	EPO; JPO;	
		or plasma adj6 (cvd or deposit\$4))	DERWENT;	
			IBM TDB	
L		<u> </u>		

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